

**DESCRIPTION**

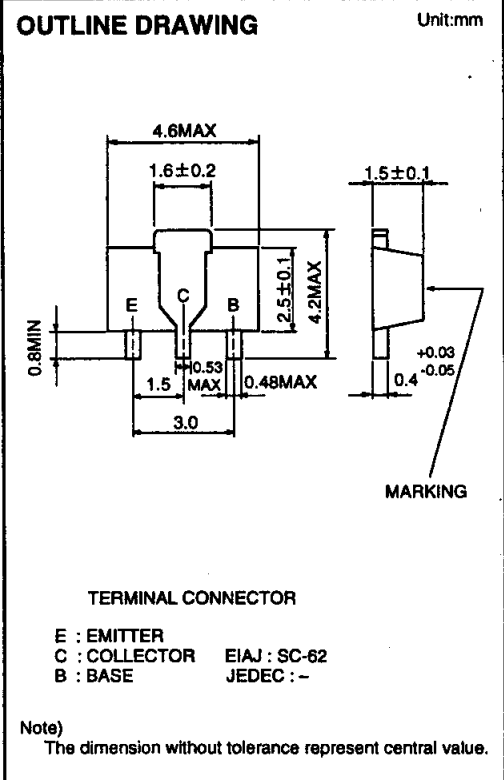
2SA1363 is a silicon PNP epitaxial type transistor designed with high collector current and high collector dissipation.  
Complementary with 2SC3443.

**FEATURE**

- High hFE hFE=150 to 800
- High collector current (Ic=2A)
- Small collector to emitter saturation voltage  
VCE(sat)=-0.17V typ (@ Ic=-1A)
- High collector dissipation Pc=500mW
- Small package for mounting

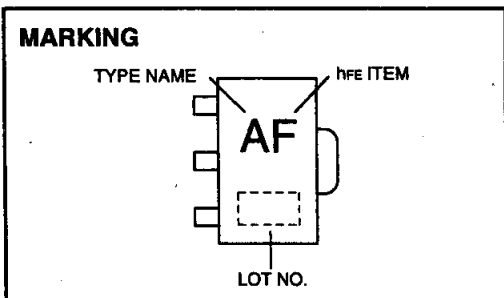
**APPLICATION**

Small type motor drive for VCR; deck, player, power supply, etc.



**MAXIMUM RATINGS (Ta=25°C)**

Symbol	Parameter	Rating	Unit
Vcbo	Collector to Base voltage	-20	V
VEBO	Emitter to Base voltage	-6	V
VCEO	Collector to Emitter voltage	-16	V
ICM	Peak Collector current	-3	A
Ic	Collector current	-2	A
Pc	Collector dissipation (Ta=25°C)	500	mW
Tj	Junction temperature	+150	°C
Tstg	Storage temperature	-55 to +150	°C



**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V(BR)CBO	C to B break down voltage	Ic=-10 μA, IE=0	-20			V
V(BR)EBO	E to B break down voltage	IE=-10 μA, IC=0	-6			V
V(BR)CEO	C to E break down voltage	IC=-2mA, RE=∞	-16			V
ICBO	Collector cut off current	VCE=-16V, IE=0			-0.2	μA
IEBO	Emitter cut off current	VEB=-4V, IC=0			-0.2	μA
hFE *	DC forward current gain	VCE=-4V, IC=100mA	150		800	—
VCE(sat)	C to E saturation voltage	IC=-1A, IB=-50mA		-0.17	-0.3	V
ft	Gain band width product	VCE=-2V, IE=10mA		80		MHz
Cob	Collector output capacitance	VCE=-10V, IE=0, f=1MHz		42		pF

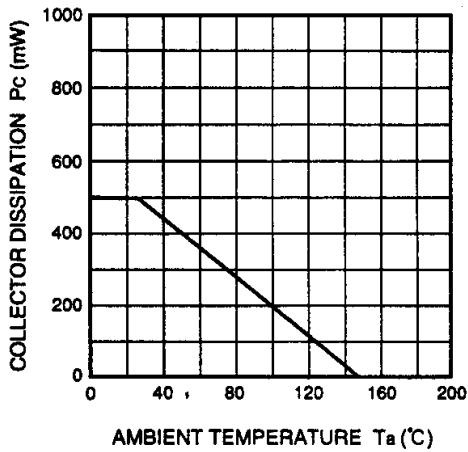
\* : It shows hFE classification in right table.

Marking	AE	AF	AG
hFE	150 to 300	250 to 500	400 to 800

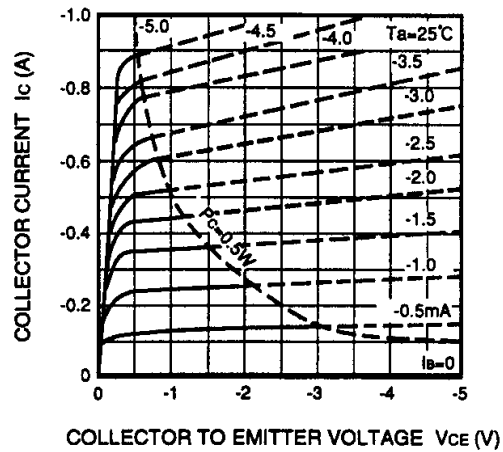
FOR HIGH CURRENT DRIVE APPLICATION  
SILICON PNP EPITAXIAL TYPE

### TYPICAL CHARACTERISTICS

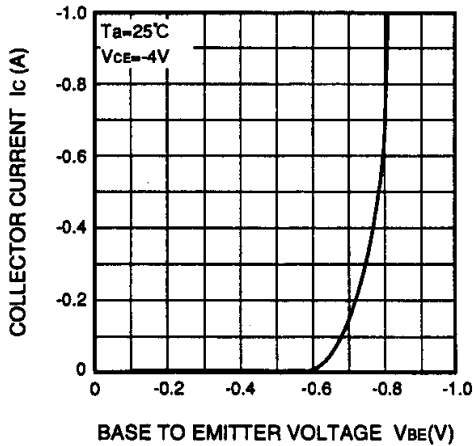
COLLECTOR DISSIPATION VS.  
AMBIENT TEMPERATURE



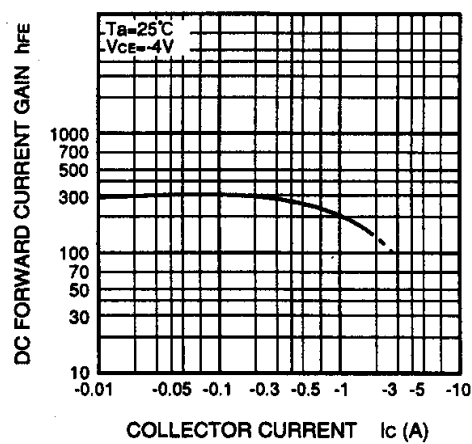
COMMON EMITTER OUTPUT



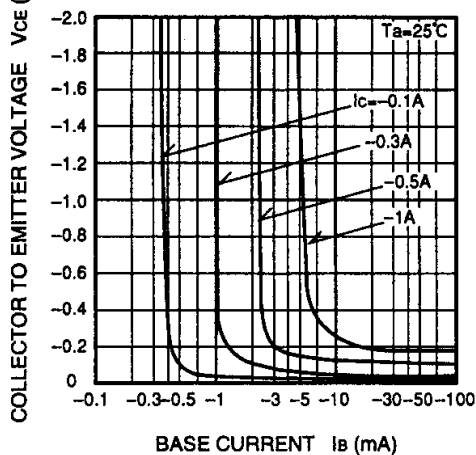
COMMON EMITTER TRANSFER



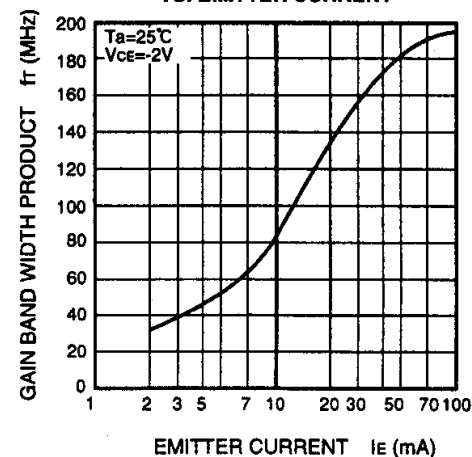
DC FORWARD CURRENT GAIN  
VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION  
VOLTAGE VS. BASE CURRENT



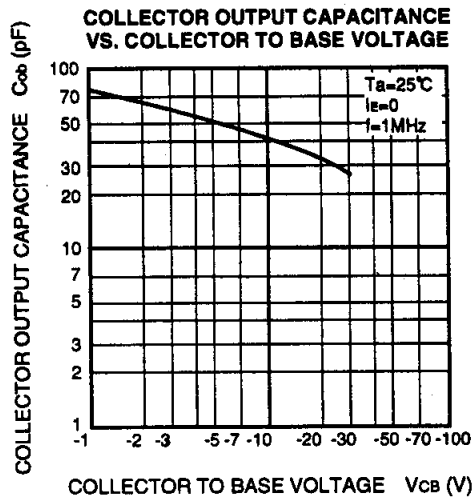
GAIN BAND WIDTH PRODUCT  
VS. EMITTER CURRENT



<SMALL-SIGNAL TRANSISTOR>

**2SA1363**

FOR HIGH CURRENT DRIVE APPLICATION  
SILICON PNP EPITAXIAL TYPE



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